

DESCRIPTION

- Excellent Safe Operating Area
- DC Current Gain-
: $h_{FE}=20-70@I_C = -4A$
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = -1.1V(Max)@ I_C = -4A$
- Complement to Type 2N3055

APPLICATIONS

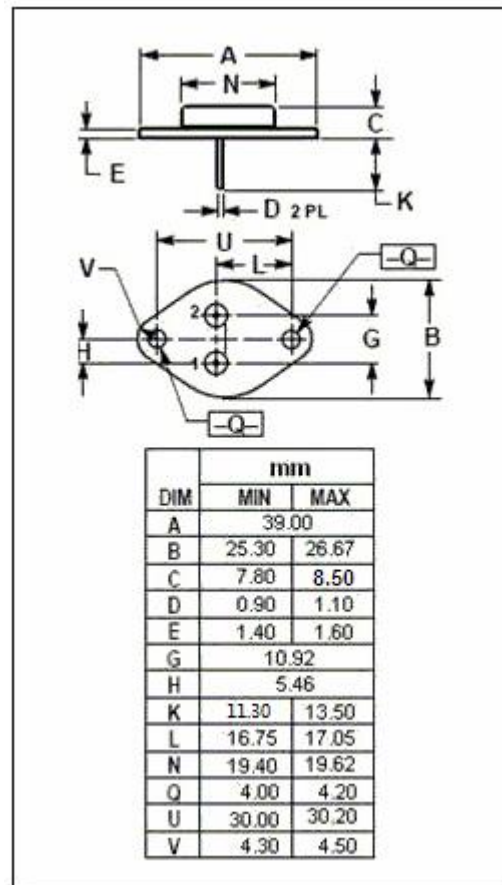
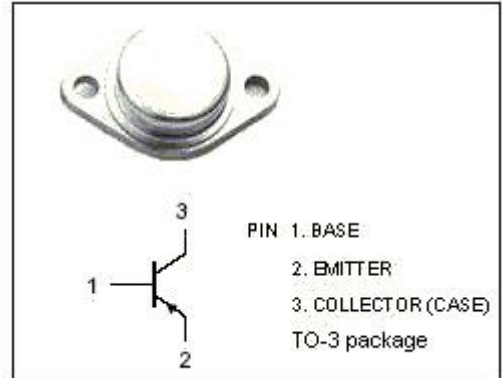
- Designed for general-purpose switching and amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-15	A
I_B	Base Current	-7	A
P_C	Collector Power Dissipation @ $T_C=25^\circ C$	115	W
T_J	Junction Temperature	200	$^\circ C$
T_{stg}	Storage Temperature	-65~200	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.52	$^\circ C/W$



ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{CEQ(SUS)}	Collector-Emitter Sustaining Voltage	I _C = -50mA ; I _B = 0	-65		V
V _{CBO}	Collector- Base Voltage	I _C = -1mA ; I _E = 0	-70		V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = -4A ; I _B = -0.4A		-1.1	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = -10A ; I _B = -3.3A		-3.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -4A ; V _{CE} = -4V		-1.5	V
I _{CEO}	Collector Cutoff Current	V _{CE} = -30V ; I _B = 0		-0.7	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -7.0V ; I _C =0		-5.0	mA
h _{FE-1}	DC Current Gain	I _C = -4A ; V _{CE} = -4V	20	70	
h _{FE-2}	DC Current Gain	I _C = -10A ; V _{CE} = -4V	5		
f _T	Current Gain-Bandwidth Product	I _C = -0.5A ; V _{CE} = -10V ; f _{test} = 1.0MHz	2.5		MHz